

<b>PCN Number:</b>	20170928001-001	<b>PCN Date:</b>	Sep 29, 2017
<b>Title:</b>	Qualification of RFAB as an additional wafer fab site option for select devices in LBC8 process technology		
<b>Customer Contact:</b>	<a href="#">PCN Manager</a>	<b>Dept:</b>	Quality Services
<b>Proposed 1<sup>st</sup> Ship Date:</b>	Mar 29, 2018	<b>Estimated Sample Availability:</b>	Date provided at sample request.
<b>Change Type:</b>			
<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Assembly Process
<input type="checkbox"/>	Design	<input type="checkbox"/>	Electrical Specification
<input type="checkbox"/>	Test Site	<input type="checkbox"/>	Packing/Shipping/Labeling
<input checked="" type="checkbox"/>	Wafer Bump Site	<input type="checkbox"/>	Wafer Bump Material
<input checked="" type="checkbox"/>	Wafer Fab Site	<input type="checkbox"/>	Wafer Fab Materials
		<input type="checkbox"/>	Part number change

### PCN Details

#### Description of Change:

This change notification is to announce the qualification of RFAB as an additional wafer fab site option for the LBC8 devices listed in the product affected section of this document.

Current Sites				Additional Sites			
Current Fab Site	Fab Process	Bump Site	Wafer Diameter	Additional Fab Site	Fab Process	Bump Site	Wafer Diameter
DP1DM5	LBC8	DBUMP	200 mm	RFAB	LBC8	Clark-BP	300 mm

Qual details are provided in the Qual Data Section.

#### Reason for Change:

Continuity of Supply

#### Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

#### Changes to product identification resulting from this PCN:

##### Current:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DP1DM5	DM5	USA	Dallas

##### New:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
<b>RFAB</b>	<b>RFB</b>	<b>USA</b>	<b>Richardson</b>

Sample product shipping label (not actual product label)



MADE IN: Malaysia  
2DC: 2d:

MSL 2 / 260C / 1 YEAR	SEAL DT
MSL 1 / 235C / UNLIM	03/29/04

OPT:  
ITEM: 39  
**LBL: 5A (L)T0:1750**




(1P) SN74LS07NSR  
(Q) 2000 (D) 0336  
(31T) LOT: 3959047MLA  
(4W) TKY (1T) 7523483S12  
(P)  
(2P) REV: (V) 0033317  
(20L) CS0: SHP (21L) CC0: USA  
(22L) AS0: MLA (23L) AC0: MYS

#### Product Affected:

LM536253QRNLRQ1	LM53625LQRNLRQ1	LM536353QRNLRQ1	LM53635LQRNLRQ1
LM536253QRNLTQ1	LM53625LQRNLTQ1	LM536353QRNLTQ1	LM53635LQRNLTQ1
LM536255QRNLRQ1	LM53625MQRNLRQ1	LM536355QRNLRQ1	LM53635MQRNLRQ1

LM536255QRNLQ1	LM53625MQRNLQ1	LM536355QRNLQ1	LM53635MQRNLQ1
LM53625AQRNLQ1	LM53625NQRNLQ1	LM53635AQRNLQ1	LM53635NQRNLQ1
LM53625AQRNLQ1	LM53625NQRNLQ1	LM53635AQRNLQ1	LM53635NQRNLQ1

**Automotive New Product Qualification Summary  
(As per AEC-Q100 and JEDEC Guidelines)**

**LMS3655x/LMS3635xQRNLQ1 and LM53625x/LM53635xQRNLQ1 family of products  
per AEC-Q100 Rev H Grade 1  
Approved 10-Jul-2017**

**Product Attributes**

Attributes	Qual Device: LMS3655AMQRNLQ1	Qual Device: LM53635LQRNLQ1
Automotive Grade Level	Grade 1	Grade 1
Operating Temp Range	-40 to +125 C	-40 to +125 C
Product Function	Power Management	Power Management
<b>Die Attributes</b>		
Wafer Fab Supplier	RFAB/CLARK-BUMP	RFAB/CLARK-BUMP
Wafer Diameter (mm)	300	300
Wafer Process Technology	LBC8MV	LBC8MV
Die Revision	A1	B0
<b>Package Attributes</b>		
Assembly Site	UTAC (NSE)	NSE / CLARK AT
Package Type	QFN/SON Hotrod	QFN/SON Hotrod
Package Designator	RNL	RNL
Ball/Lead Count	22	22
Package Size (mils)	157.48 X 196.85	157.48 X 196.85
Lead Frame Material	Cu	Cu
Leadframe Plating Composition	Matte SN	Matte SN

- QBS: Qual By Similarity  
- Qual Devices are qualified at LEVEL2-260C

**Qualification Results**

**Data Displayed as: Number of lots / Total sample size / Total failed**

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LMS3655AMQRNLQ1	QBS Product Reference: LM53635LQRNLQ1
<b>Test Group A – Accelerated Environment Stress Tests</b>								
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	MSL2/260C	ATE	3/231/0	3/1180/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96/hours @ 130C/85%	-	3/231/0
AC	A3	JEDEC JESD22-A102	3	77	Autoclave 121C	96/hours @ 121C	-	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500/Cycles @ -65C/150C	3/231/0	3/231/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle, -40/125C	1000/Cycles @ -40C/125C	-	1/45/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp Storage Bake 175C	500/hours @ 175C	-	3/231/0
<b>Test Group B – Accelerated Lifetime Simulation Tests</b>								
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 150C	408/hours @150C	1/77/0	3/231/0
ELFR	B2	AEC Q100-008	3	800	Life Test, 150C	48 hours @ 150C	QBS to process technology level: 3/2400/0 on TI proprietary part number	
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	N/A
<b>Test Group C – Package Assembly Integrity Tests</b>								
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear (Cpk>1.67)	-	N/A	N/A
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull (Cpk>1.67)	-	N/A	N/A
SD	C3	JEDEC JESD22-B102	1	15	Surface Mount Solderability >95% Lead Coverage	-	-	1 lot Pass
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	-	-	3 lots Pass
SBS	C5	AEC Q100-010	3	50	Solder Ball Shear (Cpk>1.67)	Solder Balls	N/A	N/A
LI	C6	JEDEC JESD22-B105	1	50	Lead Integrity	-	N/A	N/A
<b>Test Group D – Die Fabrication Reliability Tests</b>								
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	Completed Per Process Technology Requirements	

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LMS3655AMQRNLQ1	QBS Product Reference: LM53635LQRNLQ1
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	-
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	-
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	-
Test Group E – Electrical Verification Tests								
HBM	E2	AEC Q100-002	1	3	ESD - HBM - Q100	500V, 1000V, 1500V, 2000V, 2500V	1/3/0	1/3/0
CDM	E3	AEC Q100-011	1	3	ESD - CDM - Q100	500V, 750V, 1000V	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-up	25C, 125C	1/6/0	1/6/0

**A1 (PC): Preconditioning:**

Performed for THB, Biased HAST, AC, uHAST & TC samples, as applicable.

**Ambient Operating Temperature by Automotive Grade Level:**

Grade 0 (or E): -40°C to +150°C

Grade 1 (or Q): -40°C to +125°C

Grade 2 (or T): -40°C to +105°C

Grade 3 (or L): -40°C to +85°C

**E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):**

Room/Hot/Cold: HTOL, ED

Room/Hot: THB/HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

**Green/Pb-free Status:**

Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	<a href="mailto:PCNAmericasContact@list.ti.com">PCNAmericasContact@list.ti.com</a>
Europe	<a href="mailto:PCNEuropeContact@list.ti.com">PCNEuropeContact@list.ti.com</a>
Asia Pacific	<a href="mailto:PCNAsiaContact@list.ti.com">PCNAsiaContact@list.ti.com</a>
Japan	<a href="mailto:PCNJapanContact@list.ti.com">PCNJapanContact@list.ti.com</a>